

Application No.: 10/087,744

Docket No.: M4065.0485/P485

REMARKS

Applicants respectfully request entry of this Preliminary Amendment prior to examination on the merits of the application. Claims 1-4, 6-13, 16-21, 24, 27-32, 35-41 and 44-50 are now pending in the application. Applicants respectfully request allowance of the pending claims.

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Respectfully submitted,

By 

Thomas J. D'Amico

Registration No. 28,371

Salvatore P. Tamburo

Registration No. 45,153

DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicants

Version with Markings to Show Changes Made

1. (Amended) A method of sensing a stored value of a programmable conductor random access memory element, the method comprising:

setting a row line and a column line associated with said memory element to respective voltage levels such that no current flows through said memory element;

changing the voltage at one of said row line and said column line to a level sufficient to initiate current flow through said memory element; [and]

discharging the voltage level at the other of said row line and said column line through said memory element and also through a reverse connected diode pair in series with said memory element; and

comparing the voltage on [the one] said other of said row line and said column line [that is being discharged] with a reference voltage to determine a logical state of said memory element.

6. (Amended) The method of claim [5] 2, wherein said act of setting comprises setting said row line and said column line to a voltage level approximately equal to a threshold voltage of said diode plus an additional voltage sufficient to enable a read operation of said memory element.

21. (Amended) A method of sensing a stored value of a programmable conductor random access memory element, the method comprising:

setting a plurality of row lines and a plurality of column lines associated with a memory array to a common voltage such that no current flows through said memory element;

changing the voltage at a selected row line to approximately zero volts such that a current flow is initiated from a column line associated with said memory element through said memory element and through a reverse connected diode [circuit] pair coupled to said memory element; and

comparing the voltage at said column line with a reference voltage a predetermined time after said act of changing in order to determine a logical state of said memory element.

24. (Amended) A method of sensing a stored value of a programmable conductor random access memory cell, the method comprising:

setting a column line and a row line associated with said memory cell to a common voltage level; and

reducing said voltage at said row line to a level such that a reverse connected diode [circuit] pair coupled to a programmable conductor memory element of said cell is activated and such that a voltage potential difference across said memory element is sufficient to read a logical state of said memory element, but insufficient to program said memory element.

27. (Amended) A semiconductor memory structure, comprising:

a column line and a row line associated with a programmable conductor random access memory cell;

a programmable conductor memory element, a first terminal of which is coupled to said column line and a second terminal of which is coupled to a first [terminal] side of a reverse connected diode [circuit] pair, wherein

a second [terminal] side of said reverse connected diode [circuit] pair is coupled to said row line; and

a sense amplifier for comparing a voltage on said column line with a reference voltage during a read operation to determine a logical state of said programmable conductor memory element.

36. (Amended) A processor system, comprising:

a processor; and

a semiconductor memory structure coupled to said processor, said semiconductor memory structure comprising:

a column line and a row line associated with a programmable conductor random access memory cell;

a programmable conductor memory element, a first terminal of which is coupled to said column line and a second terminal of which is coupled to a first [terminal] side of a reverse connected diode [circuit] pair, wherein

a second [terminal] side of said reverse connected diode [circuit] pair is coupled to said row line; and

a sense amplifier for comparing a voltage on said column line with a reference voltage during a read operation to determine a logical state of said programmable conductor memory element.